

DCR1003SF

Phase Control Thyristor

Replaces January 2000 version, DS4548-3.2

DS4645-6.0 July 2001

FEATURES

- Double Side Cooling
- High Surge Capability
- Low Turn-on Losses

APPLICATIONS

- High Power Converters
- High Voltage Power Supplies
- DC Motor Control

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} V _{RRM} V	Conditions
DCR1003SF18	1800	$T_{vi} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR1003SF17	1700	$I_{DRM}^{y} = I_{RRM} = 100 \text{mA},$
DCR1003SF16	1600	V_{DRM} , V_{RRM} $t_p = 10ms$,
DCR1003SF15	1500	V _{DSM} & V _{RSM} =
DCR1003SF14	1400	$V_{DRM} \& V_{RRM} + 100V$
		respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1003SF18

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

KEY PARAMETERS

 V_{DRM} 1800V $I_{T(AV)}$ 1511A I_{TSM} 26250A $dVdt^*$ 1000V/ μ s dI/dt 1000A/ μ s

^{*}Higher dV/dt selections available

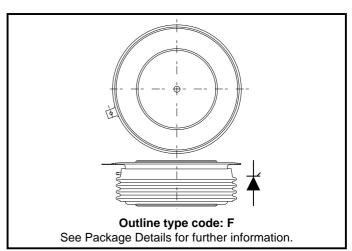


Fig. 1 Package outline



CURRENT RATINGS

 $T_{case} = 60$ °C unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units			
Double Sic	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	1511	А			
I _{T(RMS)}	RMS value	-	2374	Α			
I _T	Continuous (direct) on-state current	-	2124	А			
Single Side Cooled (Anode side)							
I _{T(AV)}	Mean on-state current	Half wave resistive load	1069	А			
I _{T(RMS)}	RMS value	-	1680	А			
I _T	Continuous (direct) on-state current	-	1411	А			

CURRENT RATINGS

 $T_{case} = 80^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units			
Double Sic	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	1180	А			
I _{T(RMS)}	RMS value	-	1852	Α			
I _T	Continuous (direct) on-state current	-	1600	Α			
Single Side Cooled (Anode side)							
I _{T(AV)}	Mean on-state current	Half wave resistive load	830	А			
I _{T(RMS)}	RMS value	-	1300	А			
I _T	Continuous (direct) on-state current	-	1050	Α			



SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	21.0	kA
l²t	I ² t for fusing	V _R = 50% V _{RRM} - 1/4 sine	2.21 x 10 ⁶	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	26.25	kA
l ² t	I ² t for fusing	V _R = 0	3.44 x 10 ⁶	A²s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance - junction to case	Double side cooled	dc	-	0.022	°C/W
		Single side cooled	Anode dc	-	0.038	°C/W
			Cathode dc	-	0.052	°C/W
R _{th(c-h)}	Thermal resistance - case to heatsink	Clamping force 19.5kN with mounting compound	Double side	-	0.004	°C/W
			Single side	-	0.008	°C/W
T _{vj}	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
-	Clamping force			18.0	22.0	kN



DYNAMIC CHARACTERISTICS

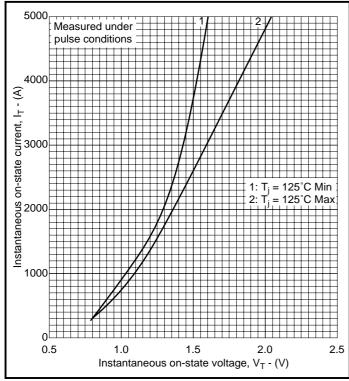
Symbol	Parameter	Conditions		Тур.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	100	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% $V_{DRM} T_j = 125^{\circ}C$.		-	1000	V/µs
-11 / -14	dI/dt Rate of rise of on-state current From 67% V_{DRM} to 1000A Gate source 1.5A $t_r = 0.5 \mu s. \ T_j = 125^{\circ}C.$	I DKM I	Repetitive 50Hz	-	500	A/μs
ai/at			Non-repetitive	-	1000	A/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	0.86	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.25	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, Gate source 30V, 15Ω Rise time 0.5μs, $T_j = 25$ °C		-	1.1	μs
t _q	Turn-off time	$I_T = 800A$, $t_p = 1ms$, $T_j = 125$ °C, $V_{RM} = 50V$, $dI_{RR}/dt = 20A/\mu s$, $V_{DR} = 50\%$ V_{DRM} , $dV_{DR}/dt = 20V/\mu s$ linear		110	200	μs
I _L	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		-	350	mA
I _H	Holding current	$T_j = 25^{\circ}C$, $R_{g-k} = \infty$		-	230	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	3.5	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	200	mA
$V_{\sf GD}$	Gate non-trigger voltage	At 67% V _{DRM} T _{case} = 125°C	0.25	V
I _{GD}	Gate non-trigger current	At 67% V _{DRM} T _{case} = 125°C	-	А
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	٧
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	٧
V_{RGM}	Peak reverse gate voltage		5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	30	А
P _{GM}	Peak gate power	See table, gate characteristics curve	150	W
P _{G(AV)}	Mean gate power		10	W



CURVES



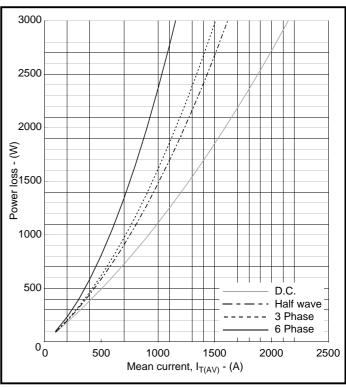


Fig.2 Maximum (limit) on-state characteristics

Fig.3 Dissipation curves

V_{TM} Equation:-

 $V_{TM} = A + BIn (I_T) + C.I_T + D.\sqrt{I_T}$

Where A = -1.191257

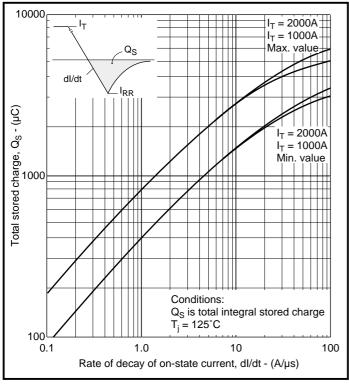
B = 0.4149874

 $C = 3.623888 \times 10^{-4}$

D = -0.02991257

these values are valid for $T_i = 125^{\circ}C$ for $I_T 500A$ to 5000A





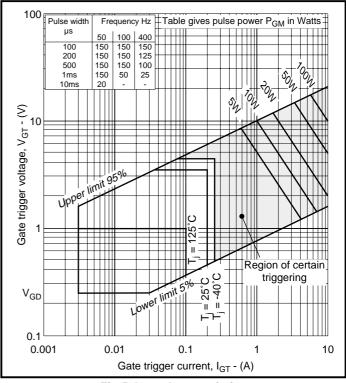


Fig.4 Stored charge

Fig.5 Gate characteristics

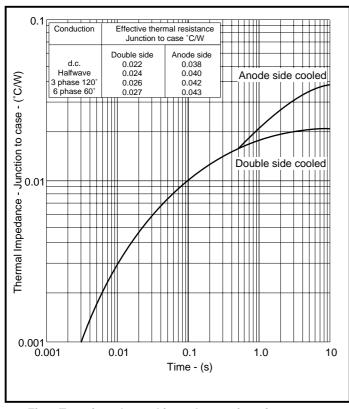


Fig.6 Transient thermal impedance - junction to case

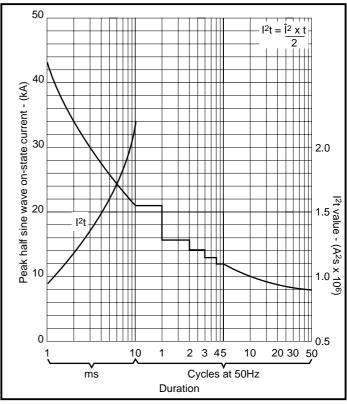
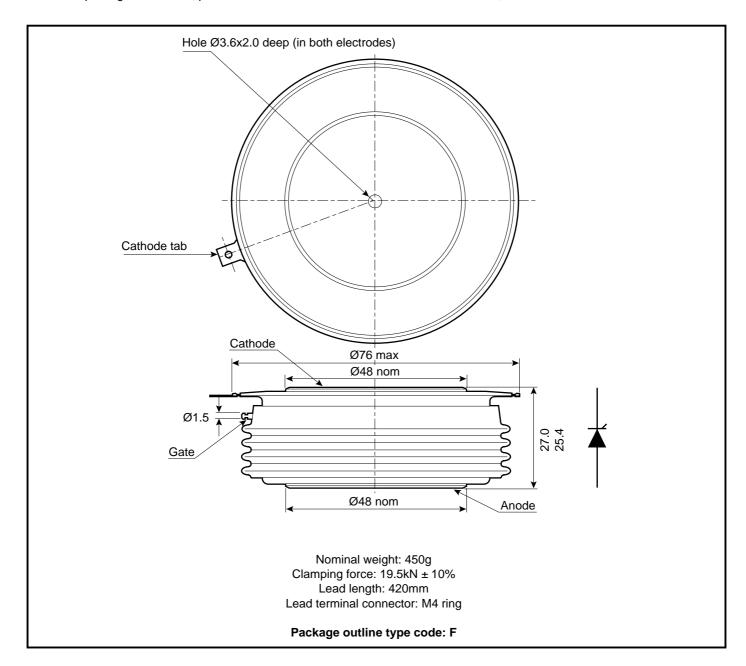


Fig.7 Surge (non-repetitive) on-state current vs time (with 50% $\rm V_{RRM}$ at $\rm T_{case}$ = 125°C)



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





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Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

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For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



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